

Tentative Data sheet 1L2,5ES-A_CP1

Active area: 2,5 x 0,6 mm²
Chip area: 4,7 x 1,6 mm²

Characteristics	Min.	Typ.	Max.	Unit
Position non-linearity		0,1	0,2	% (±)
Detector resistance	40	50	80	kΩ
Leakage current		2	10	nA
Noise current		0,4	1,0	pA/√Hz
Responsivity		3		A/W
Capacitance		1,6	2	pF
Rise time (10%-90%)		300	500	ns
Bias voltage (reverse)	5	15	20	V
Thermal drift		20	100	ppm/°C

Maximum ratings

Reverse voltage	30	V
Operating temperature	70	°C
Storage temperature	100	°C

Test conditions: Room temperature 23 °C, bias voltage 15V, light source wavelength 940 nm. Position non-linearity and thermal drift are valid within 80 % of the detector length.

Package: 4-pin DIL package, 9,9 x 5,8 mm², with protective window.

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